

## ABSTRACT OF THE DISCLOSURE

ACMOS image sensor is made such that an oxide film, a nitride film, an oxide film, and a nitride film constituting an  
5 antireflection film are stacked over the surface of a photodiode,  
and the oxide film and the nitride film are anisotropically etched,  
to thereby form sidewalls at both sides of a gate electrode  
constituting an N type MOS transistor.